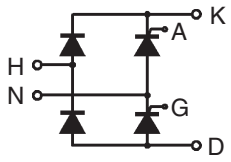
Single Phase Rectifier Bridge

I_{dAV} = 36 A
V_{RRM} = 1600 V

Preliminary data

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type
1700	1600	VGO 36-16io7



Symbol	Test Conditions		Maximum Ratings	
I_{dAV} ✶	T_H = 85°C, module		36	A
I_{dAVM} ✶	module		40	A
I_{FRMS}, I_{TRMS}	per leg		31	A
I_{FSM}, I_{TSM}	T_{VJ} = 45°C;	t = 10 ms (50 Hz), sine	320	A
	V_R = 0 V	t = 8.3 ms (60 Hz), sine	350	A
	T_{VJ} = T_{VJM}	t = 10 ms (50 Hz), sine	280	A
	V_R = 0 V	t = 8.3 ms (60 Hz), sine	310	A
I^2t	T_{VJ} = 45°C	t = 10 ms (50 Hz), sine	500	A^2s
	V_R = 0 V	t = 8.3 ms (60 Hz), sine	520	A^2s
	T_{VJ} = T_{VJM}	t = 10 ms (50 Hz), sine	390	A^2s
	V_R = 0 V	t = 8.3 ms (60 Hz), sine	400	A^2s
$(di/dt)_{cr}$	T_{VJ} = 125°C	repetitive, I_T = 50 A	150	A/µs
	f = 50 Hz, t_P = 200 µs			
	V_D = 2/3 V_{DRM}			
	I_G = 0.3 A,	non repetitive, I_T = 1/2 • I_{dAV}	500	A/µs
	di_G/dt = 0.3 A/µs			
$(dv/dt)_{cr}$	T_{VJ} = T_{VJM}; V_{DR} = 2/3 V_{DRM}		1000	V/µs
	R_{GK} = ∞; method 1 (linear voltage rise)			
V_{RGM}			10	V
P_{GM}	T_{VJ} = T_{VJM}	t_p = 30 µs	≤ 10	W
	I_T = I_{TAVM}	t_p = 500 µs	≤ 5	W
		t_p = 10 ms	≤ 1	W
P_{GAVM}			0.5	W
T_{VJ}			-40...+125	°C
T_{VJM}			125	°C
T_{stg}			-40...+125	°C
V_{ISOL}	50/60 Hz, RMS	t = 1 min	2500	V~
	I_{ISOL} ≤ 1 mA	t = 1 s	3000	V~
M_d	Mounting torque (M4)		1.5 - 2	Nm
			14 - 18	lb.in.
Weight	typ.		18	g

Data according to IEC 60747 refer to a single diode/thyristor unless otherwise stated
✶ for resistive load at bridge output. IXYS reserves the right to change limits, test conditions and dimensions.

Features

- Package with DCB ceramic base plate
- Isolation voltage 3000 V~
- Planar passivated chips
- Low forward voltage drop
- Leads suitable for PC board soldering

Applications

- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- Small and light weight

Symbol	Test Conditions		Characteristic Values		
I_R, I_D	$V_R = V_{RRM}$; $V_D = V_{DRM}$	$T_{VJ} = T_{VJM}$	≤	5	mA
		$T_{VJ} = 25°C$	≤	0.3	mA
V_T, V_F	I_T, I_F = 45 A; $T_{VJ} = 25°C$		≤	1.45	V
V_{T0}	For power-loss calculations only ($T_{VJ} = 125°C$)			0.85	V
r_T				13	mΩ
V_{GT}	V_D = 6 V;	$T_{VJ} = 25°C$	≤	1.0	V
		$T_{VJ} = -40°C$	≤	1.2	V
I_{GT}	V_D = 6 V;	$T_{VJ} = 25°C$	≤	65	mA
		$T_{VJ} = -40°C$	≤	80	mA
		$T_{VJ} = 125°C$	≤	50	mA
V_{GD}	$T_{VJ} = T_{VJM}$;	V_D = 2/3 V_{DRM}	≤	0.2	V
I_{GD}	$T_{VJ} = T_{VJM}$;	V_D = 2/3 V_{DRM}	≤	5	mA
I_L	I_G = 0.3 A; t_G = 30 µs;	$T_{VJ} = 25°C$	≤	150	mA
	di_G/dt = 0.3 A/µs;	$T_{VJ} = -40°C$	≤	200	mA
		$T_{VJ} = 125°C$	≤	100	mA
I_H	$T_{VJ} = 25°C$; V_D = 6 V; $R_{GK} = \infty$		≤	100	mA
t_{gd}	$T_{VJ} = 25°C$; V_D = 1/2 V_{DRM} I_G = 0.3 A; di_G/dt = 0.3 A/µs		≤	2	µs
t_q	$T_{VJ} = 125°C$, I_T = 15 A, t_P = 300 µs, V_R = 100 V di/dt = -10 A/µs, dv/dt = 20 V/µs, V_D = 2/3 V_{DRM}		typ.	150	µs
R_{thJC}	per thyristor (diode); DC current			1.4	K/W
	per module			0.35	K/W
R_{thJK}	per thyristor (diode); DC current			2.0	K/W
	per module			0.5	K/W
d_S	Creepage distance on surface			12.6	mm
d_A	Creepage distance in air			6.3	mm
a	Max. allowable acceleration			50	m/s^2

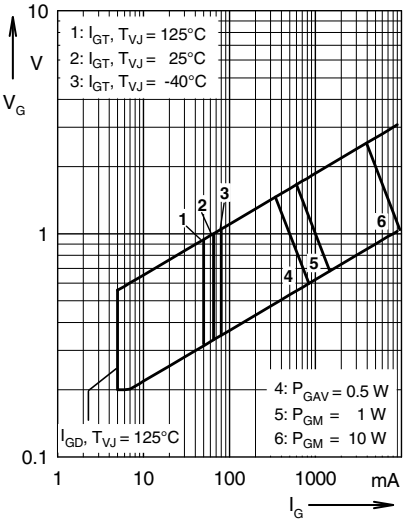


Fig. 1 Gate trigger range

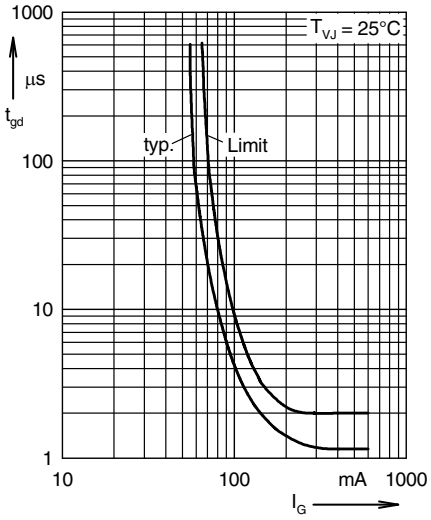


Fig. 2 Gate controlled delay time t_{gd}

Dimensions in mm (1 mm = 0.0394")